



上海双岭电子有限公司

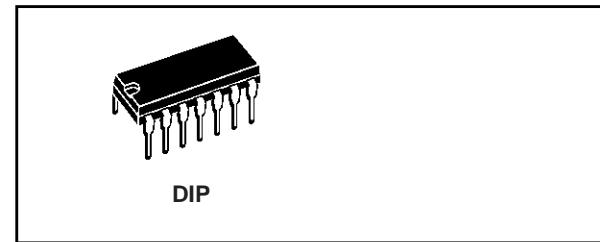
CC4068

8 INPUT NAND/AND GATE

- MEDIUM-SPEED OPERATION
 $t_{PHL}, t_{PLH} = 75\text{ns}$ (Typ.) at 10V
- BUFFERED OUTPUT
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_I = 100\text{nA}$ (MAX) AT $V_{DD} = 18\text{V}$ $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The CC4068 is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The CC4068 8 INPUT NAND/AND GATE provide the system designer with direct

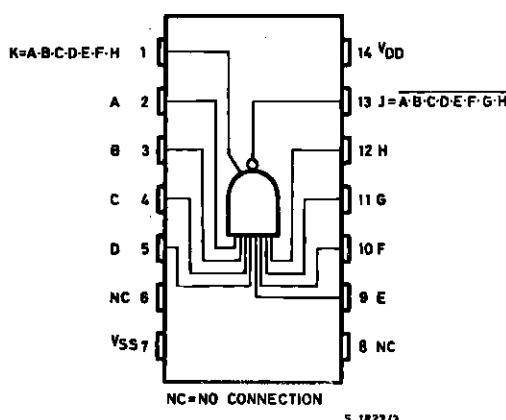


ORDER CODES

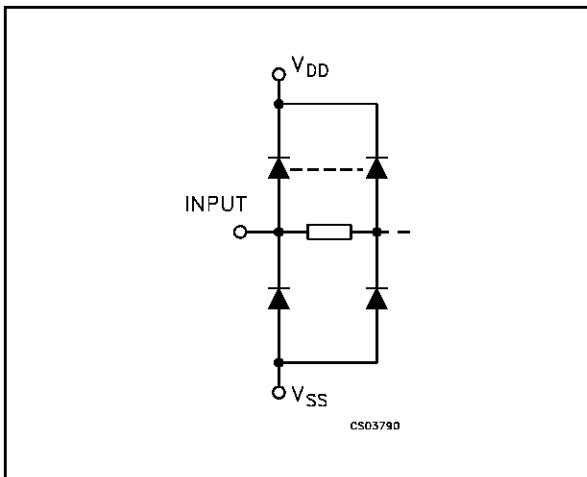
PACKAGE	TUBE	T & R
DIP	CC4068	

implementation of the positive-logic 8-input NAND and AND functions and supplements the existing family of CMOS gates.

PIN CONNECTION



INPUT EQUIVALENT CIRCUIT



TRUTH TABLES

INPUTS									OUTPUT
A	B	C	D	E	F	G	H	J (NAND)	
L	X	X	X	X	X	X	X	H	
X	L	X	X	X	X	X	X	H	
X	X	L	X	X	X	X	X	H	
X	X	X	L	X	X	X	X	H	
X	X	X	X	L	X	X	X	H	
X	X	X	X	X	L	X	X	H	
X	X	X	X	X	X	L	X	H	
X	X	X	X	X	X	X	L	H	
H	H	H	H	H	H	H	H	L	

INPUTS									OUTPUT
A	B	C	D	E	F	G	H	K (AND)	
L	X	X	X	X	X	X	X	L	
X	L	X	X	X	X	X	X	L	
X	X	L	X	X	X	X	X	L	
X	X	X	L	X	X	X	X	L	
X	X	X	X	L	X	X	X	L	
X	X	X	X	X	L	X	X	L	
X	X	X	X	X	X	L	X	L	
X	X	X	X	X	X	X	L	L	
H	H	H	H	H	H	H	H	H	

PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 3, 4, 5, 9, 10, 11, 12	A, B, C, D, E, F, G, H	Data Inputs
6, 8	NC	Not Connected
1	K	Data Output (AND)
13	J	Data Output (NAND)
7	V_{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +20	V
V_I	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 18	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value						Unit	
		V_I (V)	V_O (V)	I_{IO} (μ A)	V_{DD} (V)	$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	μA
		0/10			10		0.01	0.5		15		15	
		0/15			15		0.01	1		30		30	
		0/18			18		0.02	5		150		150	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage	0.5/4.5	<1	5	3.5				3.5		3.5		V
		1/9	<1	10	7				7		7		
		1.5/13.5	<1	15	11				11		11		
V_{IL}	Low Level Input Voltage	4.5/0.5	<1	5				1.5		1.5		1.5	V
		9/1	<1	10				3		3		3	
		13.5/1.5	<1	15				4		4		4	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I_I	Input Leakage Current	0/18	Any Input	18			$\pm 10^{-5}$	± 0.1		± 1		± 1	μA
C_I	Input Capacitance		Any Input				5	7.5					pF

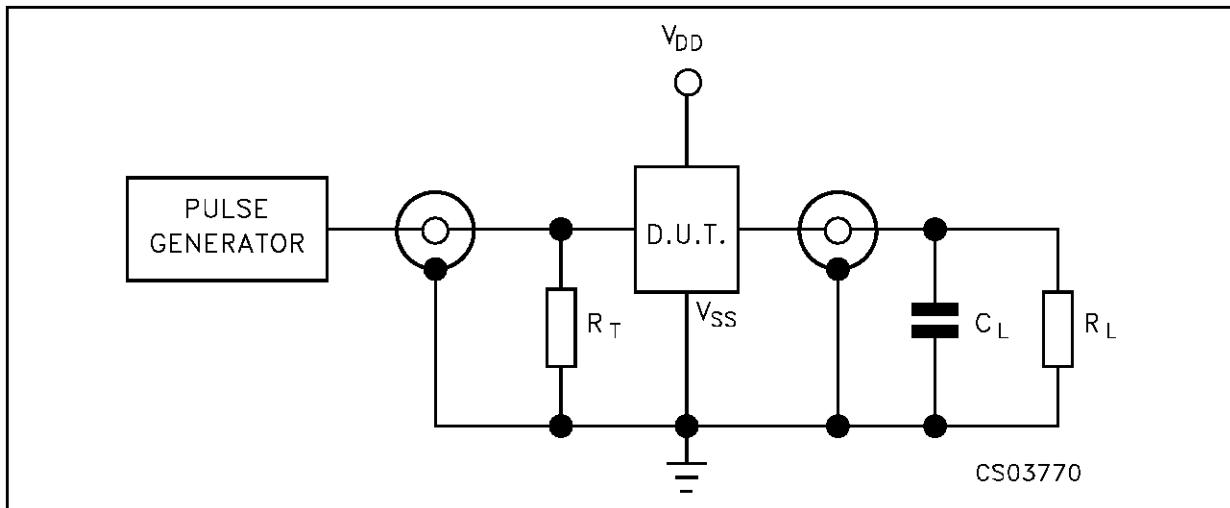
The Noise Margin for both "1" and "0" level is: 1V min. with $V_{DD}=5V$, 2V min. with $V_{DD}=10V$, 2.5V min. with $V_{DD}=15V$

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$, $C_L = 50pF$, $R_L = 200K\Omega$, $t_r = t_f = 20 \text{ ns}$)

Symbol	Parameter	Test Condition				Value (*)			Unit	
		V_{DD} (V)				Min.	Typ.	Max.		
t_{PLH} t_{PHL}	Propagation Delay Time	5						150	300	ns
		10						75	150	
		15						55	110	
t_{TLH} t_{THL}	Output Transition Time	5						100	200	ns
		10						50	100	
		15						40	80	

(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/ $^\circ C$.

TEST CIRCUIT



$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)

$R_L = 200\text{K}\Omega$

$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1 : PROPAGATION DELAY TIMES FOR K OUTPUT (AND FUNCTION) ($f=1\text{MHz}$; 50% duty cycle)

